

MAC218



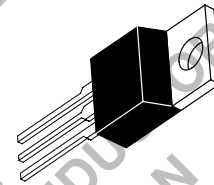
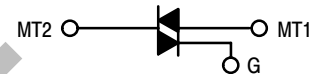
Triacs Silicon Bidirectional Thyristors

Triacs are designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 800 Volts
- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- TO-220 Construction Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC218 Series) or Four Modes (MAC218A Series)

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CASE 221A-04
(TO-220AB)
STYLE 4

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (Gate Open, T _J = 25 to 125°C) MAC218-4, MAC218A4 MAC218-6, MAC218A6 MAC218-8, MAC218A8 MAC218-10, MAC218A10	V _{DRM}	200 400 600 800	Volts
On-State Current RMS (Conduction Angle = 360°, T _C = +80°C)	I _{T(RMS)}	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T _C = 80°C, preceded and followed by rated current)	I _{TSM}	100	Amps
Fusing Current (t = 8.3 ms)	I ² t	40	A ² s
Peak Gate Power (T _C = +80°C, Pulse Width = 2 μs)	P _{GM}	16	Watts
Average Gate Power (T _C = +80°C, t = 8.3 ms)	P _{G(AV)}	0.35	Watt
Peak Gate Trigger Current (Pulse Width = 1 μs)	I _{GTM}	4	Amps
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

1.. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current ($V_D = \text{Rated } V_{DRM}$, gate open) $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I_{DRM}	— —	— —	10 2	μA mA
Peak On-State Voltage (Either Direction) ($I_{TM} = 11.3 A$ Peak; Pulse Width = 1 to 2 ms, Duty Cycle < 2%)	V_{TM}	—	1.7	2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 V_{dc}$, $R_L = 12\Omega$) Trigger Mode MT2(+), Gate(+); MT2(+), Gate(-); MT2(-), Gate(-) MT2(-), Gate(+)"A" SUFFIX ONLY	I_{GT}	— —	— —	50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)"A" SUFFIX ONLY (Main Terminal Voltage = Rated V_{DRM} , $R_L = 10 k\Omega$, $T_J = +125^{\circ}C$) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+)"A" SUFFIX ONLY	V_{GT}	— — — — 0.2 0.2	0.9 0.9 1.1 1.4 — —	2 2 2 2.5 — —	Volts
Holding Current (Either Direction) ($V_D = 24 V_{dc}$, Gate Open, Initiating Current = 200 mA)	I_H	—	—	50	mA
Critical Rate of Rise of Commutating Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11.3 A$, Commutating $di/dt = 4.1 A/ms$, Gate Unenergized, $T_C = 80^{\circ}C$)	$dv/dt(c)$	—	5	—	$V/\mu s$
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Voltage Rise, Gate Open, $T_J = 125^{\circ}C$)	dv/dt	—	100	—	$V/\mu s$

FIGURE 1 — CURRENT DERATING

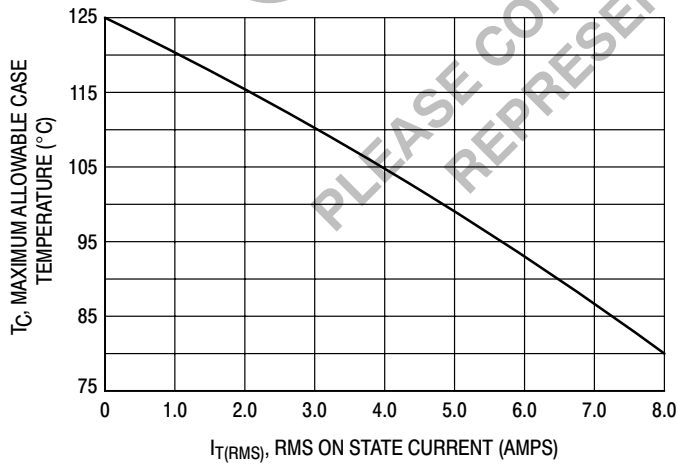
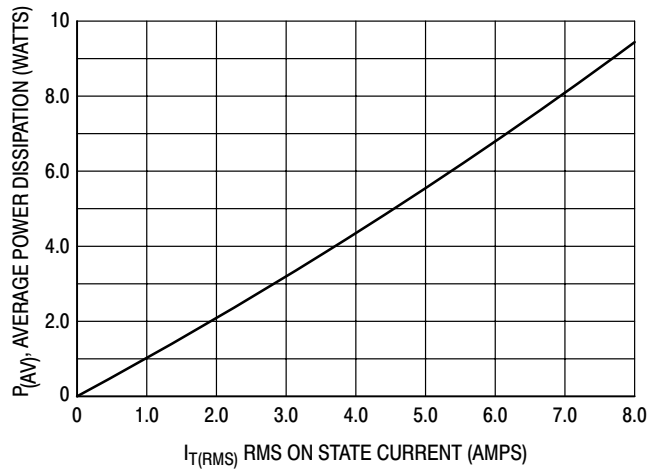


FIGURE 2 — POWER DISSIPATION



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FIGURE 3 — NORMALIZED GATE TRIGGER CURRENT

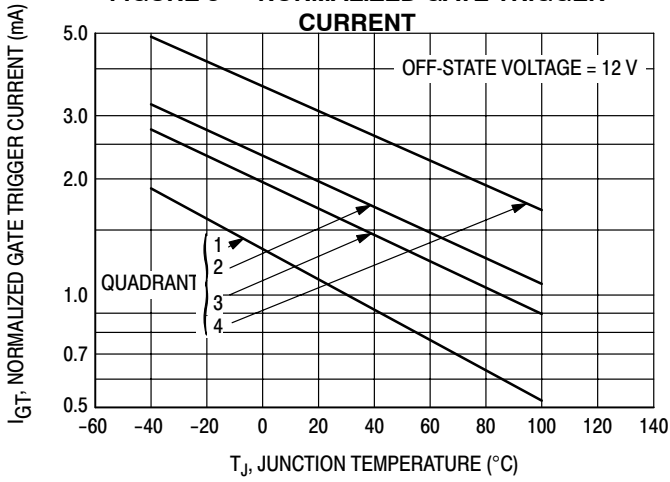


FIGURE 4 — NORMALIZED GATE TRIGGER VOLTAGE

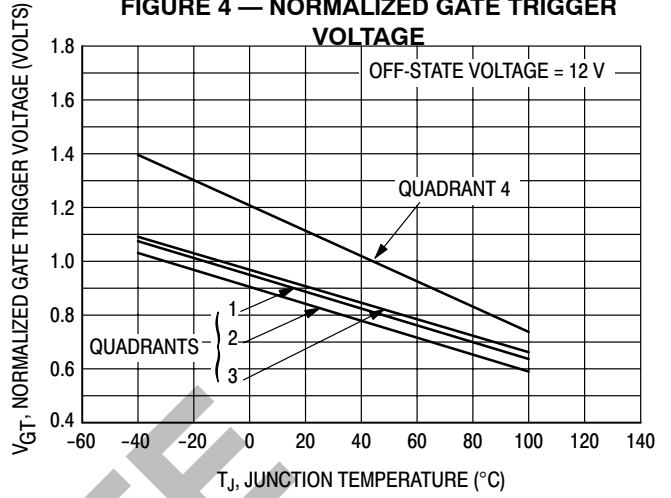
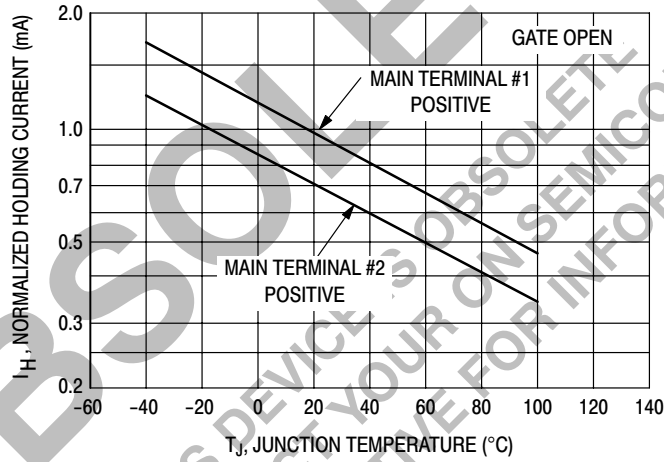


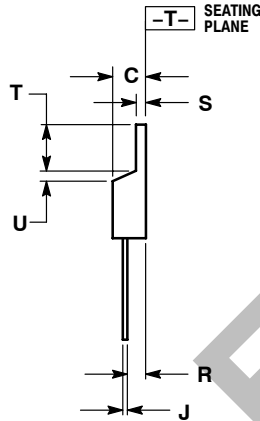
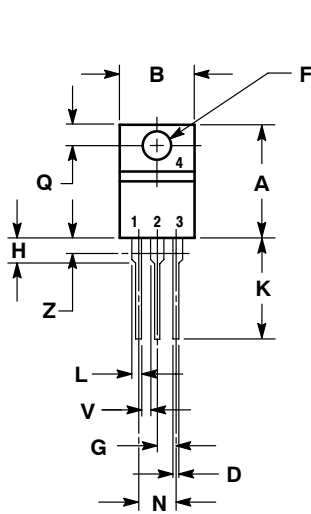
FIGURE 5 — NORMALIZED HOLDING CURRENT



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PACKAGE DIMENSIONS

CASE 221A-04 (TO-220AB)



STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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